

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE1540KA uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

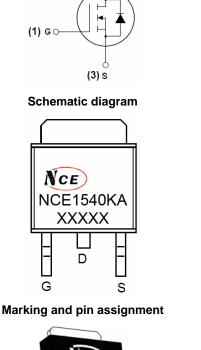
General Features

- $V_{DS} = 150V, I_D = 40A$ $R_{DS(ON)} < 45m\Omega @ V_{GS} = 10V$ (Typ:35m Ω)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED! 100% ΔVds TESTED!



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TO-252-2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE1540KA	NCE1540KA	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_c=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	Vds	150	V	
Gate-Source Voltage	Vgs	±12	V	
Drain Current-Continuous	Ι _D	40	А	
Drain Current-Continuous(Tc=100℃)	I _D (100℃)	29	А	
Pulsed Drain Current	I _{DM}	160	А	
Maximum Power Dissipation	PD	140	W	
Derating factor		0.93	W/℃	
Single pulse avalanche energy (Note 5)	E _{AS}	350	mJ	
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	്റ	



Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	1.07	°C/W	1
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Electrical Characteristics (T_c=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	150	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =150V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±12V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, I _D =250µA	0.7	1.05	1.4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =18A	-	35	45	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =18A	38	-	-	S
Dynamic Characteristics (Note4)	I					
Input Capacitance	C _{lss}		-	4300	-	PF
Output Capacitance	Coss	V_{DS} =75V, V_{GS} =0V,	-	130	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	111	-	PF
Switching Characteristics (Note 4)	· · ·					
Turn-on Delay Time	t _{d(on)}		-	14	-	nS
Turn-on Rise Time	tr	V_{DD} =30V, I_D =2A, R_L =15 Ω	-	12	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =2.5 Ω	-	45	-	nS
Turn-Off Fall Time	t _f		-	11	-	nS
Total Gate Charge	Qg			63.8	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =75V,I _D =18A, V _{GS} =4.5V		9.8	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} -4.5V		26.9	-	nC
Drain-Source Diode Characteristics	· · · · ·					
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =18A	-	-	1.2	V
Diode Forward Current (Note 2)	ls		-	-	40	Α
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 18A	-	42	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	75	-	nC

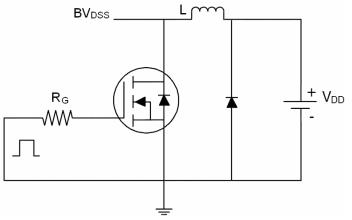
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition:Tj=25 $^{\circ}$ C,V_{DD}=50V,V_G=10V,L=0.5mH,Rg=25 Ω

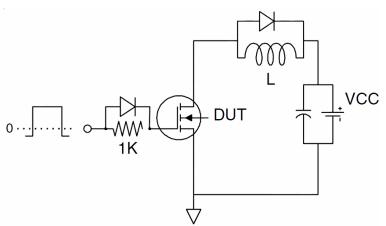


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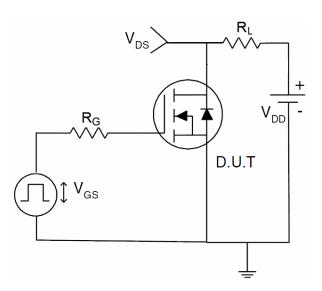
Test Circuit 1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit:





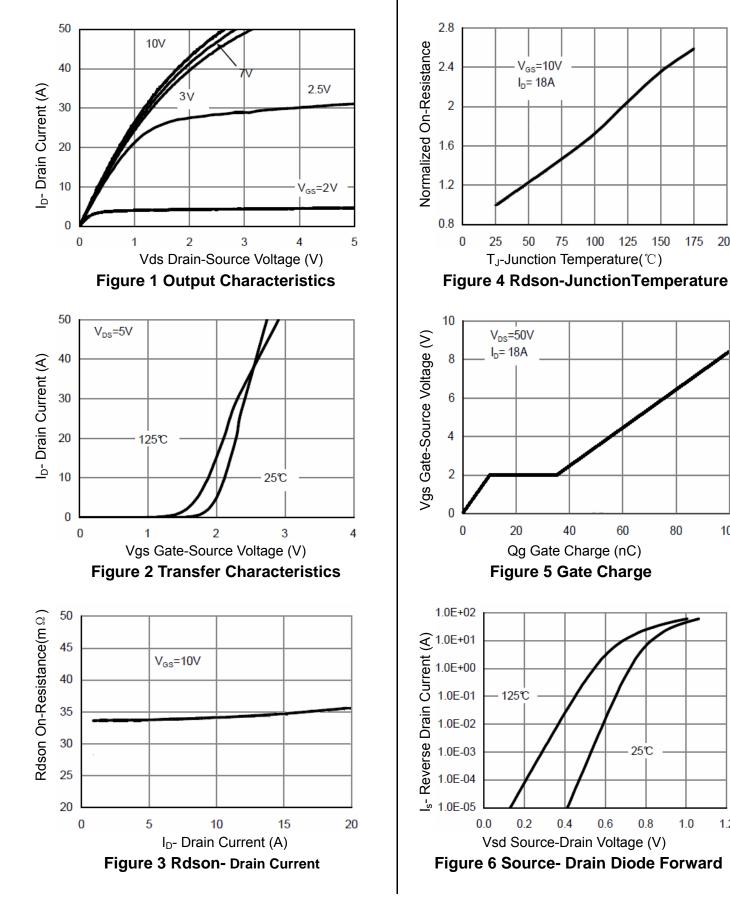
175

80

100

200

Typical Electrical and Thermal Characteristics (Curves)

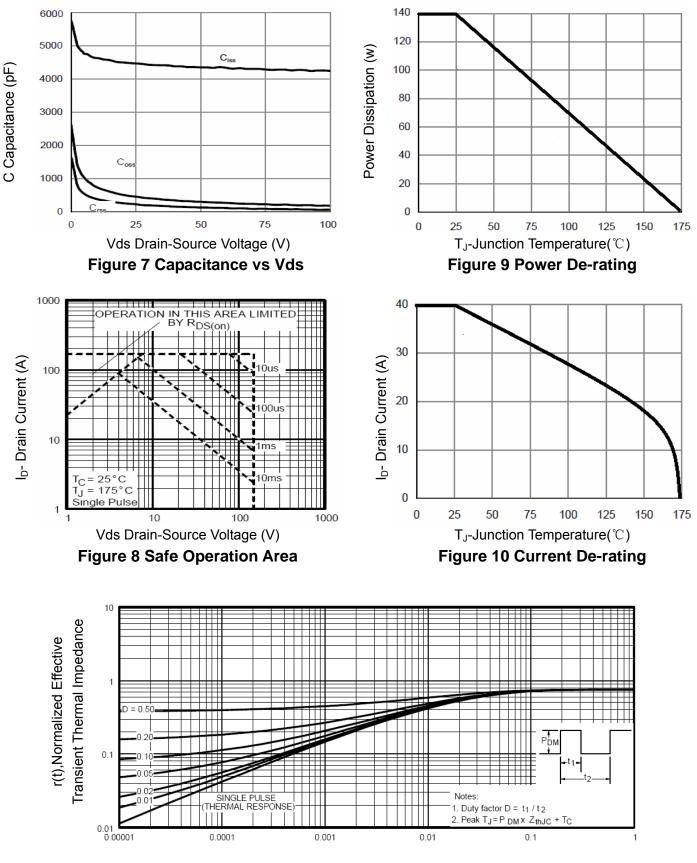


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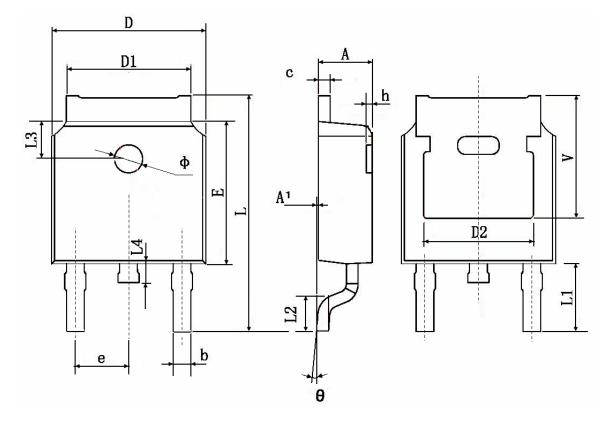


Square Wave Pluse Duration(sec) Figure 11 Normalized Maximum Transient Thermal Impedance



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TO-252 Package Information



Currente e l	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.8	330TYP.	0.190 TYP.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.90	2.900 TYP.		TYP.	
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0 °	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.35	0 TYP.	0.211 TYP.		



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